

# N-Channel 100 V (D-S) MOSFET



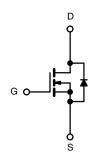
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	100				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.00383				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$	0.0045				
Q <sub>g</sub> typ. (nC)	84				
I <sub>D</sub> (A) <sup>d</sup>	150				
Configuration	Single				

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- Maximum 175 °C junction temperature
- 100 % R<sub>q</sub> and UIS tested
- $\bullet$  Very low  $Q_{gd}$  reduces power loss from passing trough  $V_{plateau}$
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

## **APPLICATIONS**

- Power supply
  - Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management
- OR-ing / e-fuse



COMPLIANT

HALOGEN

**FREE** 

N-Channel MOSFET

ORDERING INFORMATION			
Package	D <sup>2</sup> PAK (TO-263-7L)		
Lead (Pb)-free and halogen-free	SUM70042M-GE3		

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage	V <sub>DS</sub>		100	V		
Gate-source voltage		$V_{GS}$	V <sub>GS</sub> ± 20			
Continuous drain surrent (T = 150 °C)	T <sub>C</sub> = 25 °C		150 <sup>d</sup>			
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	l <sub>D</sub>	150 <sup>d</sup>	А		
Pulsed drain current (t = 100 μs)		I <sub>DM</sub> 500		7 ^		
Avalanche current		I <sub>AS</sub>	60			
Single avalanche energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	180	mJ		
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	PD	375 <sup>b</sup>	w		
	T <sub>C</sub> = 125 °C		125 <sup>b</sup>	]		
Operating junction and storage temperature ran-	ge	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient (PCB mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W	
Junction-to-case (drain)	R <sub>thJC</sub>	0.4	- C/VV	

#### **Notes**

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}$	100	-	-	V	
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.0	-	3.8	V	
Gate-body leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	—— uA	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125 ^{\circ}\text{C}$	-	-	150		
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA	
Drain-source on-state resistance a	В	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	0.00316	0.00383	Ω	
Drain-source on-state resistance "	R <sub>DS(on)</sub>	$V_{GS} = 7.5 \text{ V}, I_D = 15 \text{ A}$	-	0.00341	0.0045		
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 20 \text{ A}$	-	68	-	S	
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		-	6750	-	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	620	-		
Reverse transfer capacitance	C <sub>rss</sub>		-	18	-		
Total gate charge <sup>c</sup>	$Q_g$		-	84	126		
Gate-source charge c	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	35	-	nC	
Gate-drain charge <sup>c</sup>	$Q_{gd}$		-	9	=.		
Gate resistance	$R_g$	f = 1 MHz	0.7	1.5	2.6	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		-	21	42		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_L = 5 \Omega$	-	10	20	no	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	41	82	ns	
Fall time <sup>c</sup>	t <sub>f</sub>		-	11	22		
Drain-Source Body Diode Ratings a	nd Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)		•			
Pulsed current (t = 100 μs)	I <sub>SM</sub>		-	-	500	Α	
Forward voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.74	1.2	V	
Reverse recovery time	t <sub>rr</sub>		-	61	120	ns	
Peak reverse recovery charge	I <sub>RM(REC)</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/µs	-	4.8	9.5	Α	
Reverse recovery charge	Q <sub>rr</sub>		-	0.150	0.30	иC	

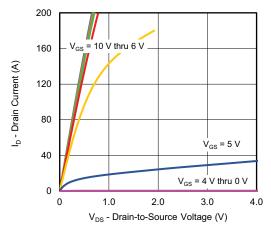
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

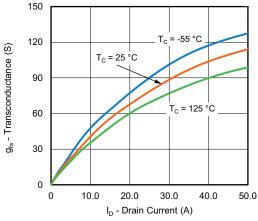
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



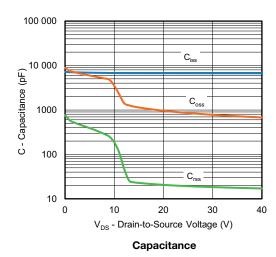
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

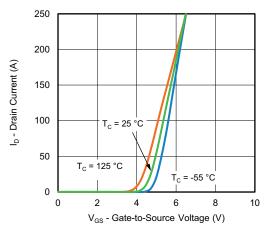


## **Output Characteristics**

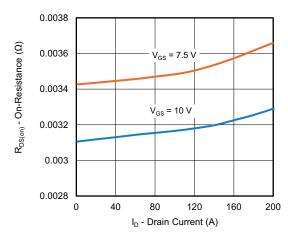


## Transconductance

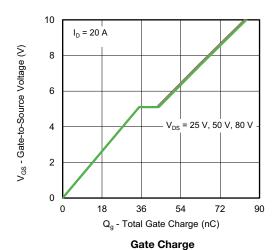




### **Transfer Characteristics**

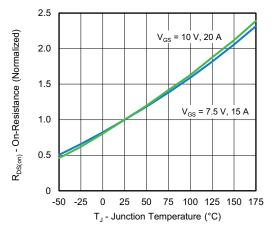


**On-Resistance vs. Drain Current** 

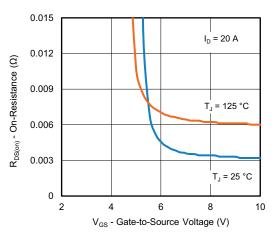




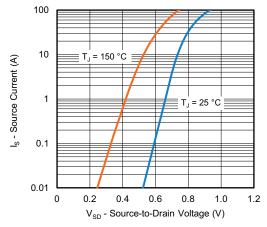
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



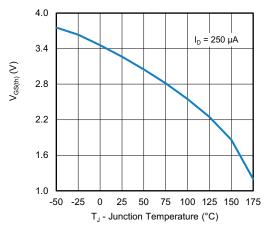
On-Resistance vs. Junction Temperature



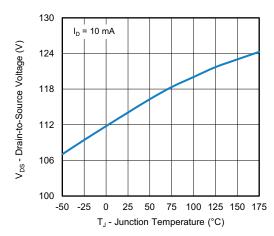
On-Resistance vs. Gate-to-Source Voltage



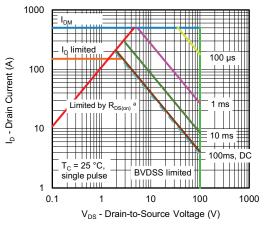
**Source Drain Diode Forward Voltage** 



**Threshold Voltage** 



Drain Source Breakdown vs. Junction Temperature

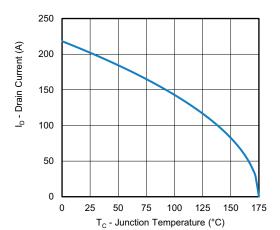


Safe Operating Area

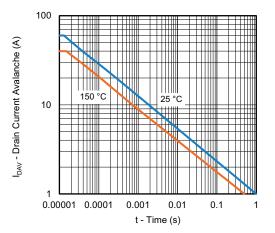
#### Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified





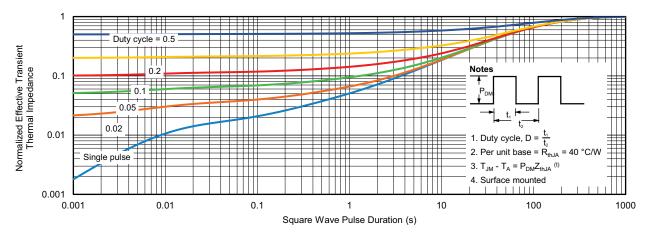
**Current De-Rating vs. Junction Temperature** 



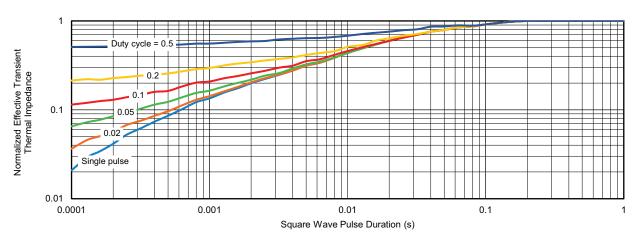
**Avalanche Current vs. Time** 



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

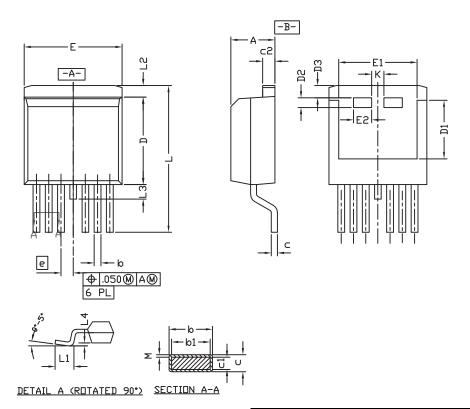
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# D<sup>2</sup>PAK (TO-263-7L) Case Outline



## **Notes**

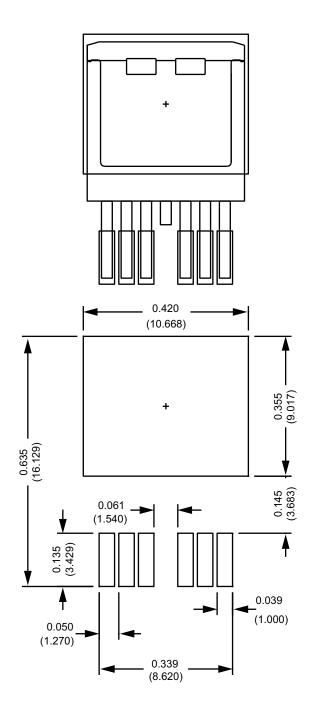
- 1. Plane B includes maximum features of heat sink tab and plastic
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils
- 3. Pin to pin coplanarity max. 4 mils
- 4. Lead thickness 25 mils
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils
- 6. For reference only
- 7. Use inches as the primary measurement
- 8. This feature is only for SUM

	INCHES		MILLIMETERS		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
c* SUB	0.012	0.018	0.305	0.457	
c* SUM	0.022	0.028	0.559	0.711	
c1	0.018	0.025	0.457	0.635	
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.260	0.280	6.604	7.112	
D2	0.046	0.050	1.168	1.270	
D3	0.045	0.055	1.143	1.397	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.072	0.078	1.829	1.981	
е	0.050 BSC		1.27 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
М	-	0.002	-	0.050	
ECN: T22-0410-Rev. D, 19-Sep-2022 DWG: 6006					

Revision: 19-Sep-2022 Document Number: 63782



# Recommended Land Pattern D<sup>2</sup>PAK (TO-263-7L)





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